NPN Triple Diffused Planar Silicon Transistor



2SC4219

400V/4A Switching Regulator Applications

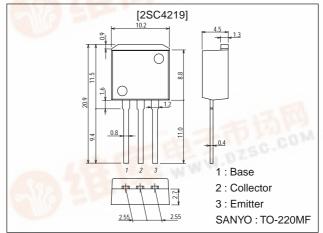
Features

- · High breakdown voltage, high reliability $(V_{CEO} \ge 400V)$.
- · Fast switching speed ($t_f=0.1\mu s$ typ).
- · Wide ASO.
- · Adoption of MBIT process.
- · Suitable for sets whose height is restricted.

Package Dimensions

unit:mm

2049C



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		500	V
Collector-to-Emitter Voltage	VCEO		400	V
Emitter-to-Base Voltage	V _{EBO}	140	7	V
Collector Current	IC		4	Α
Collector Current (Pulse)	I _{CP}	PW≤300μs, duty cycle≤10%	8	Α
Base Current	I _B	AND ARE INC. W	1.5	Α
Collector Dissipation	PC		1.65	W
		Tc=25°C	40	W
Junction Temperature	Tj	O Table	150	°C
Storage Temperature	Tstg	Com	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} =400V, I _E =0		1	10	μΑ
Emitter Cutoff Current	I _{EBO}	V _{EB} =5V, I _C =0	T-CO-		10	μΑ
DC Current Gain	*hFE1	V _{CE} =5V, I _C =0.4A	15		50	
	h _{FE} 2	V _{CE} =5V, I _C =2A	10			
	h==3	V _{CE} =5V, I _C =10mA	10			

*: The h_{FE}1 of the 2SC4219 is classified as follows. When specifying the h_{FE}1 rank, specify two ranks or more in principle.

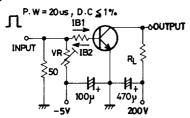
15 L 30 20 M 40 30 N 50

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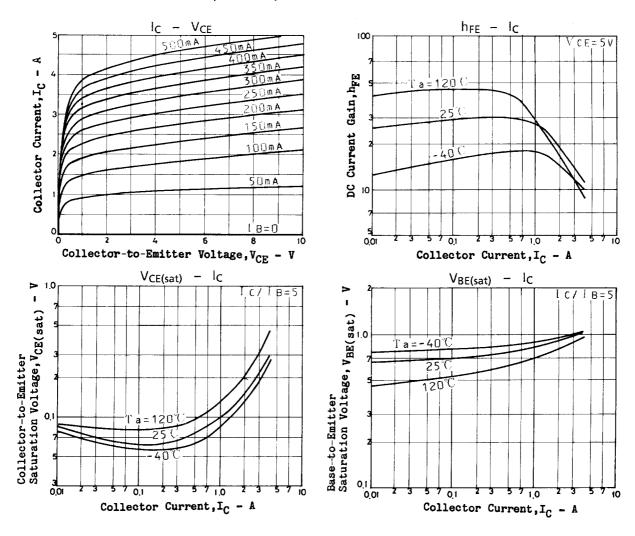
SANYO Electric Co., Ltd. Semiconductor Bussiness Headquaters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

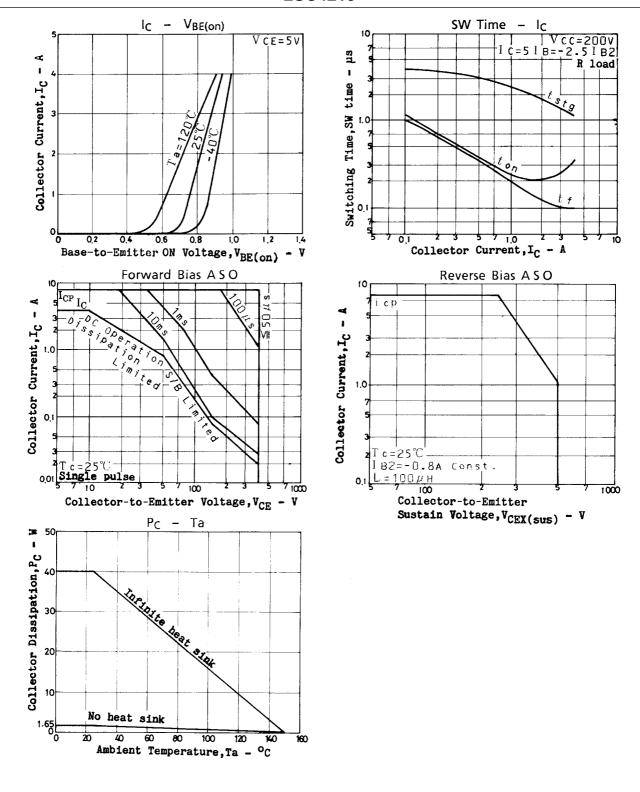
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =2A, I _B =0.4A			0.8	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =2A, I _B =0.4A			1.5	V
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =0.4A		20		MHz
Output Capacitance	C _{ob}	V _{CB} =10V, f=1MHz		50		pF
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =1mA, I _E =0	500			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =5mA, R _{BE} =∞	400			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =1mA, I _C =0	7			V
Collector-to-Emitter Sustain Voltage	VCEX(sus)	I _C =2A, I _{B1} =0.2A, L=1mH, I _{B2} =-0.8A, clamped	400			V
Turn-ON Time	ton	I_{C} =3A, I_{B1} =0.6A, I_{B2} =-1.2A, R_{L} =66.6 Ω , V_{CC} =200 V			0.5	μs
Storage Time	t _{stg}	I_{C} =3A, I_{B1} =0.6A, I_{B2} =-1.2A, R_{L} =66.6 Ω , V_{CC} =200 V			2.5	μs
Fall Time	t _f	I_{C} =3A, I_{B1} =0.6A, I_{B2} =-1.2A, R_{L} =66.6 Ω , V_{CC} =200 V			0.3	μs

Switching Time Test Circuit



Unit (resistance: Ω , capacitance: F)





2SC4219

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